# Preparation of Co2FeSn Heusler alloy films and magnetoresistance of Fe/MgO/Co2FeSn magnetic tunnel junctions

<table>
<thead>
<tr>
<th>著者（英）</th>
<th>Masaaki Tanaka, Y Ishikawa, Y Wada, S Hori, A Murata, S Horii, Y Yamanishi, Ko Mibu, K Kondou, T Ono, S Kasai</th>
</tr>
</thead>
<tbody>
<tr>
<td>ジャーナル名</td>
<td>Journal of Applied Physics</td>
</tr>
<tr>
<td>卷</td>
<td>111</td>
</tr>
<tr>
<td>号</td>
<td>5</td>
</tr>
<tr>
<td>ページ</td>
<td>053902-1-053902-4</td>
</tr>
<tr>
<td>年</td>
<td>2012-03-01</td>
</tr>
<tr>
<td>URL</td>
<td><a href="http://id.nii.ac.jp/1476/00005611/">http://id.nii.ac.jp/1476/00005611/</a></td>
</tr>
<tr>
<td>doi</td>
<td>10.1063/1.3688324(<a href="http://dx.doi.org/10.1063/1.3688324">http://dx.doi.org/10.1063/1.3688324</a>)</td>
</tr>
</tbody>
</table>

著作権 © 2012 American Institute of Physics. この記事は個人の使用に限られ、他の利用は事前に著者及びアメリカラインスオブフィジックスの承認が必要です。
Preparation of Co2FeSn Heusler alloy films and magnetoresistance of Fe/MgO/Co2FeSn magnetic tunnel junctions
M. A. Tanaka, Y. Ishikawa, Y. Wada, S. Hori, A. Murata et al.

Citation: J. Appl. Phys. 111, 053902 (2012); doi: 10.1063/1.3688324
View online: http://dx.doi.org/10.1063/1.3688324
View Table of Contents: http://jap.aip.org/resource/1/JAPIAU/v111/i5
Published by the American Institute of Physics.

Related Articles
Injection locking at zero field in two free layer spin-valves
Appl. Phys. Lett. 102, 102413 (2013)

Micromagnetic simulation of high-power spin-torque oscillator in half-metallic Heusler alloy spin valve nanopillar
AIP Advances 3, 032132 (2013)

Ultrathin magnetic oxide EuO films on Si(001) using SiOx passivation—Controlled by hard x-ray photoemission spectroscopy

Heterojunction of multiferroic HoMnO3 on Nb-doped SrTiO3

The manipulation of magnetic properties by resistive switching effect in CeO2/La0.7(Sr0.1Ca0.9)0.3MnO3 system

Additional information on J. Appl. Phys.
Journal Homepage: http://jap.aip.org/
Journal Information: http://jap.aip.org/about/about_the_journal
Top downloads: http://jap.aip.org/features/most_downloaded
Information for Authors: http://jap.aip.org/authors

ADVERTISEMENT
Preparation of $\text{Co}_2\text{FeSn}$ Heusler alloy films and magnetoresistance of $\text{Fe/MgO/Co}_2\text{FeSn}$ magnetic tunnel junctions


1Department of Engineering Physics, Electronics and Mechanics, Nagoya Institute of Technology, Nagoya, Aichi 466-8555, Japan
2Institute for Chemical Research, Kyoto University, Uji, Kyoto 611-0011, Japan
3Magnetic Materials Center, National Institute for Materials Science, Tsukuba, Ibaraki 305-0047, Japan

(Received 19 July 2011; accepted 24 January 2012; published online 1 March 2012)

To obtain magnetic tunnel junctions (MTJs) composed of non-equilibrium alloy, $\text{Co}_2\text{FeSn}$ films were prepared by atomically controlled alternate deposition at various substrate temperatures. X-ray diffraction patterns and Mössbauer spectra clarify that $\text{Co}_2\text{FeSn}$ films in the Heusler alloy phase can be realized by growing at a substrate temperature of 250°C or below. Phase separation into cubic $\text{CoSn}$, hexagonal $\text{CoSn}$ and cubic $\text{CoFe}$ phases occurs in films grown at substrate temperatures 300°C or greater. $\text{Fe/MgO/Co}_2\text{FeSn}$ MTJs were prepared with the $\text{Co}_2\text{FeSn}$ layer grown at various substrate temperatures. The MTJs with the ferromagnetic $\text{Co}_2\text{FeSn}$ layer grown at a substrate temperature of 250°C showed tunnel magnetoresistance ratios of 72.2% and 43.5% at 2 K and 300 K, respectively. © 2012 American Institute of Physics. [http://dx.doi.org/10.1063/1.3688324]

I. INTRODUCTION

Tunnel magnetoresistance (TMR) in magnetic tunnel junctions (MTJs) is of interest for use in spin electronic devices, e.g. read heads in hard disk drives and magnetic random access memory, etc.1,2 One promising way to achieve high TMR ratio is to use highly spin-polarized materials as ferromagnetic electrodes of MTJs. Heusler alloys, which have the composition $\text{X}_2\text{YZ}$ (X and Y: transition metals; Z: group III, IV or V element), are predicted to be highly spin-polarized materials3,4 and have been used for MTJ electrodes.5–7 Recently, TMR ratios of over 300% at room temperature were reported for MTJs with $\text{Co}_2\text{FeAl}_{0.5}\text{Si}_{0.5}/\text{MgO}/\text{Co}_2\text{FeAl}_{0.5}\text{Si}_{0.5}$ and $\text{Co}_2\text{FeAl}/\text{MgO}/\text{CoFe}$ structures.8,9 Large TMR effects may also be obtained in MTJs using new ferromagnetic alloys which have not yet been tested. Some Heusler-type alloys which cannot be fabricated in thermal equilibrium because of phase separation may show high spin-polarization. On the other hand, it is expected that thin films of non-equilibrium alloy can be fabricated using atomically controlled alternate deposition.10 We have already demonstrated that Heusler alloy films prepared by this technique have more uniform magnetic environments than bulk alloys prepared by arc-melting.11

In this paper, we report fabrication of $\text{Co}_2\text{FeSn}$ Heusler alloy films with an L2₁ ordered structure using atomically controlled alternate deposition. The physical properties of $\text{Co}_2\text{FeSn}$ have not been experimentally studied so far, because it is difficult to fabricate $\text{Co}_2\text{FeSn}$ alloy. Zhang et al. demonstrated that bulk $\text{Co}_2\text{Mn}_1\text{Fe}_{2}\text{Sn}$ Heusler alloys with $x > 0.5$ prepared by arc-melting contain impurities such as $\text{Co}_2\text{Sn}_2$ and $\text{CoFe}$ and tend to decompose when $x$ increases.12 Judging from these results, $\text{Co}_2\text{FeSn}$ Heusler alloy cannot be fabricated by arc melting method because of phase separation. On the other hand, since $\text{Co}_2\text{FeSn}$ contains $^{119}\text{Sn}$ and $^{57}\text{Fe}$ nuclei, local magnetism can be investigated using Mössbauer spectroscopy. Therefore, MTJs with a $\text{Co}_2\text{FeSn}$ layer allows us to clarify the relation between local magnetism and TMR effects. X-ray diffraction patterns and Mössbauer spectra indicate that $\text{Co}_2\text{FeSn}$ films in the Heusler alloy phase can be fabricated at substrate temperatures of 250°C or below and that phase separation into cubic $\text{CoSn}$, hexagonal $\text{CoSn}$ and cubic $\text{CoFe}$ phases occurs in films grown at higher substrate temperatures. MTJs were also prepared with $\text{Co}_2\text{FeSn}$ grown at various substrate temperatures. TMR measurements for $\text{Fe/MgO/Co}_2\text{FeSn}$ MTJs, where the $\text{Co}_2\text{FeSn}$ layer was grown at the substrate temperature of 250°C, showed the TMR ratios of 72.2% and 43.5% at 2 K and 300 K, respectively.

II. EXPERIMENTAL

$\text{Co}_2\text{FeSn}$ films were prepared at various substrate temperatures, $T_s$ on a Cr buffer layer grown on MgO (001) substrates using an electron beam deposition system. $\text{Co}_2\text{FeSn}$ films 39 nm thick were grown by depositing one atomic layer of Co, and half an atomic layer of Fe and Sn alternately in a controlled manner. The compositions of the $\text{Co}_2\text{FeSn}$ films were examined by an electron probe micro analyzer. The crystal structures were characterized by reflection high energy electron diffraction and X-ray diffraction (XRD) with Cu Kα radiation. To obtain information on local magnetism and structures, $^{119}\text{Sn}$ and $^{57}\text{Fe}$ Mössbauer spectra were measured by means of conversion electron Mössbauer spectroscopy. The spectra were fitted with a magnetically split sextet with a distribution of magnetic hyperfine fields. MgO (5 nm)/Cr (30 nm)/Fe (20 nm)/MgO (2.4 nm)/$\text{Co}_2\text{FeSn}$ (19.6 nm)/Co (25 nm)/Cr (1 nm) layered structures for MTJs were prepared on MgO (001) substrates. The bottom
ferromagnetic Fe layer was deposited at room temperature and annealed at 350°C to improve the crystallographic quality. After deposition of the MgO barrier layer at room temperature, the top ferromagnetic Co2FeSn layer was prepared by depositing one atomic layer of Co, half an atomic layer of Fe and Sn alternately at substrate temperatures of 200, 250, 300 and 400°C. The interface atoms at the Co2FeSn layer on the MgO barrier were designed to be Co. The Co (25 nm) layer was deposited on the Co2FeSn layer to reinforce an antiparallel configuration of magnetization between the lower Fe and upper Co2FeSn layers. The layered structures were fabricated into MTJs comprising ellipse-shaped pillars with an in-plane size of several μm and Ar ion etching. Magnetoresistance measurements were carried out using a standard dc four-probe method.

III. RESULTS AND DISCUSSION

Figure 1(a) shows θ-2θ XRD patterns of the Co2FeSn films. The peaks at about 31° and 63° in each XRD pattern can be attributed to L21 Co2FeSn (002) and Co2FeSn (004) reflections. These peaks may also be from CoSn, CoFe and/or FeSn with B2 or A2 structure. The dependence of lattice parameters perpendicular to the plane of the films estimated from the position of the peaks around 2θ = 31° on the substrate temperature is shown in Fig. 1(b). The lattice parameter varies from 5.90 Å to 5.81 Å with increasing substrate temperature. As clarified from the Mössbauer spectra discussed in the following paragraphs, Co2FeSn in the Heusler phase becomes dominant when the growth temperature is under 250°C. A peak from hexagonal CoSn (110) is observed at 2θ = 33° for the films grown at Ts ≥ 500°C. The full widths at half maxima (FWHM) of θ-2θ XRD of the peaks around 2θ = 31° as a function of the substrate temperature are shown in Fig. 1(c). The degree of (001) epitaxy decreases a little for the Co2FeSn films grown at Ts ≥ 450°C. This may be because an equilibrium hexagonal CoSn phase separated out in the films grown at Ts ≥ 450°C. From the intensity ratio of the Co2FeSn (111) and (002) diffraction peaks in polar plots, the degree of L21 order of the Co2FeSn films grown at around 250°C is estimated to be about 16%.

Figure 2(a) shows 119Sn conversion electron Mössbauer spectra, 2(b) shows distributions of hyperfine field at the 119Sn sites, 2(c) 57Fe conversion electron Mössbauer spectra and Fig. 2(d) shows distributions of hyperfine field at the 57Fe sites. A broad peak is observed at fields higher than 10 T in the 119Sn hyperfine-field distributions of the films deposited at Ts ≤ 400°C. Another peak is observed at around 2 T in the 119Sn hyperfine-field distributions of the films grown at Ts ≥ 300°C. This peak becomes sharper with increasing substrate temperature. On the other hand, a single peak at around 35 T can be seen in the 57Fe hyperfine-field distribution for all the Co2FeSn films. The width of this peak becomes sharper with increasing substrate temperature.

The significant difference in 119Sn hyperfine-field distributions as a function of growth temperature can be explained by phase separation in the Co2FeSn films grown at high substrate temperatures. Judging from the 119Sn Mössbauer spectra of bulk Co2Mn1-xFe2Sn Heusler alloys prepared by arc-melting, the peak at around or above 10 T in Fig. 2(b) can be attributed to the L21-ordered Co2FeSn Heusler alloy. The broad distribution in hyperfine field implies that the degree of L21 order is not particularly high, which is consistent with the estimation from the XRD patterns. For comparison with the Co2FeSn films, non-equilibrium films of B2 CoSn alloy were prepared by atomically controlled alternate deposition at a substrate temperature of 100°C. The 119Sn Mössbauer spectrum and hyperfine-field distribution at the 119Sn sites of the B2 CoSn film are shown in Fig. 3. There is a peak at around 2 T in the hyperfine-field distribution. The spectrum is similar to the spectra of the Co2FeSn films grown at high substrate temperatures. Therefore, it can be concluded that phase separation into CoSn and CoFe occurs in the films grown at higher substrate temperatures. There is slight asymmetry in the profiles of 119Sn Mössbauer spectra for the Co2FeSn films grown at higher substrate temperatures. This is because not only B2 CoSn but hexagonal CoSn exists in these films. We note that peaks from B2 FeSn are not observed in the spectra.

On the other hand, the 57Fe Mössbauer spectra for all the films show no significant differences. The peak at around 35 T in the hyperfine-field distribution at the 57Fe sites in the films grown at low substrate temperatures is attributed to an ordered Co2FeSn Heusler alloy. Because the Mössbauer spectrum of cubic CoFe also has a peak at around 35 T, there is no significant difference in the 57Fe Mössbauer spectra when phase separation occurs. Considering all the Mössbauer spectroscopic results, it is evident that Co2FeSn films...
in the Heusler alloy phase are obtained when the films are grown at a substrate temperature of 250 °C. Phase separation into hexagonal CoSn, cubic CoSn and cubic CoFe phases occurs in the films grown at higher substrate temperatures.

Since the conditions for making Co$_2$FeSn films in the Heusler alloy phase were determined, MTJs using the Co$_2$FeSn alloy as a ferromagnetic layer were prepared to measure their TMR. Figure 4 shows the θ-2θ XRD patterns of the MgO/Cr/Fe/MgO/Co$_2$FeSn/Co/Cr layered structures. Co$_2$FeSn (002), Co$_2$FeSn (004) and Fe (002) peaks are observed, indicating that the Co$_2$FeSn and Fe electrodes have been grown epitaxially with (001) orientation on the MgO (001) substrate.

Figure 5(a) shows magnetoresistance curves of the Fe/MgO/Co$_2$FeSn MTJs at a bias voltage of 1 mV at 300 K. TMR ratios of 25.5%, 43.5%, 27.0% and 11.0% are observed for MTJs with the Co$_2$FeSn layer grown at substrate temperatures of 200, 250, 300 and 400 °C, respectively. The resistance area product values of the MTJs are about 10$^5$ Ωµm$^2$.

The largest TMR ratio is realized for the sample grown at 250 °C, where the Co$_2$FeSn layer has no second phases such as cubic CoSn and cubic CoFe. The TMR ratios of the MTJs with the Co$_2$FeSn layer grown at higher substrate temperatures become smaller. This may be because of phase separation into hexagonal CoSn, cubic CoSn and cubic CoFe phases and disorder of the crystal structure in the Co$_2$FeSn layers. It has been reported that TMR effect is suppressed by the existence of disordered phases in ferromagnetic layers of MTJs with Heusler alloys. We have shown the relation between phases in the ferromagnetic layers of the MTJs and the suppression of TMR effect using Mössbauer spectroscopy. These results indicate that Mössbauer spectroscopy is applicable to optimize MTJs fabrication conditions.

The magnetoresistance at a bias voltage of 1 mV at 2 K for the MTJ with Co$_2$FeSn layer grown at a substrate temperature of 250 °C is shown in Fig. 5(b). The MTJ exhibits a TMR ratio of 72.2% at 2 K. The spin polarization of the Co$_2$FeSn layer estimated from the TMR ratio at 2 K is 0.55, assuming the spin polarization of Fe to be 0.48. Note that the band calculation of Co$_2$FeSn (Ref. 18) shows that Co$_2$FeSn has negative spin polarization at the Fermi level, whereas the spin polarization values observed experimentally are positive.
This difference in the sign of spin polarization between theoretical and experimental results can be attributed to the difference between the energy band of bulk Co$_2$FeSn and that at the Co$_2$FeSn interface with the MgO barrier. Some previous researches\textsuperscript{19,20} demonstrated that the spin polarization at the ferromagnetic-electrode interfaces with the barrier rather than that of the bulk ferromagnetic electrodes dominates the spin polarization of tunneling electrons. In this way, we have succeeded in obtaining the TMR effect for MTJs with a non-equilibrium ferromagnetic layer.

**IV. CONCLUSION**

In this study, we fabricated Co$_2$FeSn films using atomically controlled alternate deposition at various substrate temperatures. X-ray diffraction patterns and Mössbauer spectra clarify that Co$_2$FeSn films in the Heusler alloy phase can be fabricated at substrate temperatures of 250°C or below, and that B2 or hexagonal CoSn and B2 or A2 CoFe phases separate out at substrate temperatures of 300°C or more. The MTJs with Fe/MgO/Co$_2$FeSn structure, where the Co$_2$FeSn layer was grown at a substrate temperature of 250°C show TMR ratios of 72.2% and 43.5% at 2 K and 300 K, respectively. We have demonstrated that non-equilibrium material can be used as ferromagnetic layers for MTJs.

**ACKNOWLEDGMENTS**

This work was supported by Grant-in-Aid for Scientific Research in Priority Areas “Creation and Control of Spin Current” from the Ministry of Education, Culture, Sports, Science and Technology of Japan. This work was also supported by Collaborative Research Program of Institute for Chemical Research, Kyoto University (Grant No. 2010-43), Institute of Ceramics Research and Education, Nagoya Institute of Technology and The Nitto Foundation.

\textsuperscript{13}L. Häggström, T. Ericsson, and R. Wäppling, Phys. Scr., 11, 94 (1975).